



30V N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD17556Q5B

FEATURES

- Extremely Low Resistance
- Ultralow Q_q and Q_{qd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

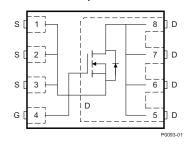
APPLICATIONS

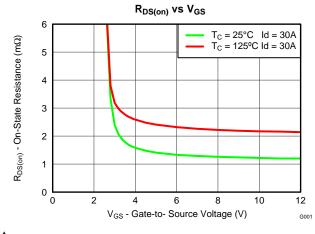
- Point-of-Load Synchronous Buck in Networking, Telecom, and Computing Systems
- · Synchronous Rectification
- Active ORing and Hotswap Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in synchronous rectification and other power conversion applications.







PRODUCT SUMMARY

$T_A = 25^{\circ}$	C unless otherwise stated	TYPICAL V	UNIT		
V_{DS}	Drain to Source Voltage 30				
Q_g	Gate Charge Total (4.5V) 30				
Q_{gd}	Gate Charge Gate to Drain	7.5		nC	
D	Drain to Source On Resistance	$V_{GS} = 4.5V$	1.5	mΩ	
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V	1.2	mΩ	
V _{GS(th)}	Threshold Voltage 1.4				

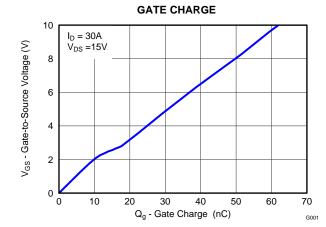
ORDERING INFORMATION

Device	Package	Media	Qty	Ship		
CSD17556Q5B	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel		

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	±20	V
	Continuous Drain Current (Package limited), T _C = 25°C	100	А
I _D	Continuous Drain Current (Silicon limited), T _C = 25°C	215	A
	Continuous Drain Current ⁽¹⁾	34	Α
I_{DM}	Pulsed Drain Current, T _A = 25°C ⁽¹⁾⁽²⁾	214	Α
P _D	Power Dissipation ⁽¹⁾	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 100A$, $L = 0.1 mH$, $R_G = 25\Omega$	500	mJ

- (1) Typical $R_{\theta JA}=42^{\circ} C/W$ on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



ATA.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
naracteristics	·	•			
Drain to Source Voltage	$V_{GS} = 0V, I_{DS} = 250\mu A$	30			V
Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 24V			1	μΑ
Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = 20V			100	nA
Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	1.15	1.4	1.65	V
Dunin to Course On Bonistones	V _{GS} = 4.5V, I _{DS} = 40A		1.5	1.8	mΩ
Drain to Source On Resistance	V _{GS} = 10V, I _{DS} = 40A		1.2	1.4	mΩ
Transconductance	V _{DS} = 15V, I _{DS} = 40A		197		S
: Characteristics	·	•			
Input Capacitance			5400	7020	pF
Output Capacitance			1770	2310	pF
Reverse Transfer Capacitance	1 - 11/11/2		68	88	pF
Series Gate Resistance			0.7	1.4	Ω
Gate Charge Total (4.5V)			30	39	nC
Gate Charge Gate to Drain	15)/ 1 404		7.5		nC
Gate Charge Gate to Source	$V_{DS} = 15V, I_{DS} = 40A$		11		nC
Gate Charge at Vth			6.1		nC
Output Charge	V _{DS} = 15V, V _{GS} = 0V		48		nC
Turn On Delay Time			14		ns
Rise Time	$V_{DS} = 15V, V_{GS} = 4.5V,$		26		ns
Turn Off Delay Time	$I_{DS} = 40A, R_G = 2\Omega$		27		ns
Fall Time			12		ns
haracteristics					
Diode Forward Voltage	I _{SD} = 40A, V _{GS} = 0V		0.8	1	V
Reverse Recovery Charge	V 45V L 40A 3V/4 000A/		68		nC
Reverse Recovery Time	$v_{DD} = 15 V$, $I_F = 40 A$, $a I/a t = 300 A/\mu s$		36		ns
	Drain to Source Voltage Drain to Source Leakage Current Gate to Source Leakage Current Gate to Source Threshold Voltage Drain to Source On Resistance Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Series Gate Resistance Gate Charge Total (4.5V) Gate Charge Gate to Drain Gate Charge Gate to Source Gate Charge at Vth Output Charge Turn On Delay Time Rise Time Turn Off Delay Time Fall Time Diode Forward Voltage Reverse Recovery Charge	Drain to Source Voltage $V_{GS} = 0V$, $I_{DS} = 250\mu A$ Drain to Source Leakage Current $V_{GS} = 0V$, $V_{DS} = 24V$ Gate to Source Leakage Current $V_{DS} = 0V$, $V_{GS} = 20V$ Gate to Source Threshold Voltage $V_{DS} = V_{GS}$, $I_{DS} = 250\mu A$ Drain to Source On Resistance $V_{DS} = V_{DS}$, $V_{DS} = 250\mu A$ Transconductance $V_{GS} = 10V$, $I_{DS} = 40A$ Characteristics Input Capacitance Input Capacitance $V_{DS} = 15V$, V_{DS	Drain to Source Voltage V _{GS} = 0V, I _{DS} = 250µA 30 Drain to Source Leakage Current V _{GS} = 0V, V _{DS} = 24V Gate to Source Leakage Current V _{DS} = 0V, V _{DS} = 20V Gate to Source Threshold Voltage V _{DS} = 0V, V _{DS} = 250µA 1.15 Drain to Source On Resistance V _{GS} = 4.5V, I _{DS} = 40A 1.15 Transconductance V _{DS} = 15V, I _{DS} = 40A 1.15 Characteristics Input Capacitance V _{GS} = 0V, V _{DS} = 15V, I _{DS} = 40A Output Capacitance V _{GS} = 0V, V _{DS} = 15V, I _{DS} = 40A Reverse Transfer Capacitance V _{GS} = 0V, V _{DS} = 15V, I _{DS} = 40A Series Gate Resistance V _{DS} = 15V, I _{DS} = 40A Gate Charge Gate to Drain V _{DS} = 15V, I _{DS} = 40A Gate Charge Gate to Source V _{DS} = 15V, V _{GS} = 0V Gate Charge at Vth V _{DS} = 15V, V _{GS} = 0V Output Charge V _{DS} = 15V, V _{GS} = 4.5V, I _{DS} = 40A, R _G = 2Ω Turn Off Delay Time I _{DS} = 40A, R _G = 2Ω Fall Time I _{DS} = 40A, V _{GS} = 0V Naracteristics Diode Forward Voltage I _{DS} = 40A, V _{GS} = 0V Naracteristics	Drain to Source Voltage V _{GS} = 0V, I _{DS} = 250μA 30 Drain to Source Leakage Current V _{GS} = 0V, V _{DS} = 24V Gate to Source Leakage Current V _{DS} = 0V, V _{GS} = 20V Gate to Source Threshold Voltage V _{DS} = 0V, V _{GS} = 250μA 1.15 1.4 Drain to Source On Resistance V _{DS} = V _{GS} , I _{DS} = 250μA 1.15 1.4 Drain to Source On Resistance V _{DS} = 15V, I _{DS} = 40A 1.5 Transconductance V _{DS} = 15V, I _{DS} = 40A 197 Characteristics Input Capacitance 5400 Output Capacitance 5400 Output Capacitance 5400 Reverse Transfer Capacitance 5400 Series Gate Resistance 0.7 Gate Charge Total (4.5V) 30 Gate Charge Gate to Drain 7.5 Gate Charge Gate to Source 11 Gate Charge at Vth 6.1 Output Charge V _{DS} = 15V, V _{GS} = 0V 48 Turn On Delay Time 14 Rise Time V _{DS} = 15V, V _{GS} = 4.5V,	Drain to Source Voltage V _{GS} = 0V, I _{DS} = 250μA 30 Drain to Source Leakage Current V _{GS} = 0V, V _{DS} = 24V 1 Gate to Source Leakage Current V _{DS} = 0V, V _{DS} = 24V 100 Gate to Source Threshold Voltage V _{DS} = 0V, V _{DS} = 250μA 1.15 1.4 1.65 Drain to Source On Resistance V _{DS} = 4.5V, I _{DS} = 40A 1.5 1.8 Transconductance V _{DS} = 15V, I _{DS} = 40A 1.2 1.4 Transconductance V _{DS} = 15V, I _{DS} = 40A 1.7 1.4 Characteristics Input Capacitance V _{DS} = 15V, I _{DS} = 40A 1.7 2310 Reverse Transfer Capacitance 5400 7020 Reverse Transfer Capacitance 5400 7020 Reverse Gate Resistance 0.7 1.4 Gate Charge Gate to Drain 7.5 30 Gate Charge Gate to Source 11 6.1 Gate Charge at Vth 6.1 0 Output Charge V _{DS} = 15V, V _{GS} = 0V 48 Turn On Delay Time 10 26 Turn Of

THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

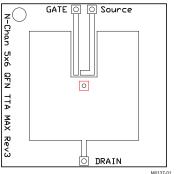
	PARAMETER	MIN	TYP	MAX	TINU
$R_{\theta JC}$	Thermal Resistance Junction to Case (1)			1.3	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1)(2)			50	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

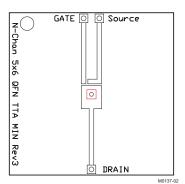
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Max $R_{\theta JA} = 50^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 125^{\circ} C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

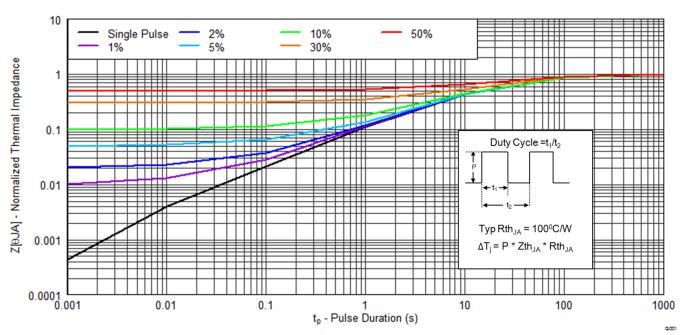


Figure 1. Transient Thermal Impedance

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2

1.8

1.6

1.4

1.2

1

0.8

0.6 -75

V_{GS(th)} - Threshold Voltage (V)



TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

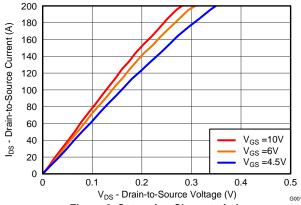


Figure 2. Saturation Characteristics

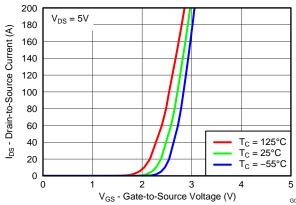
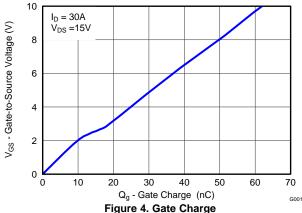
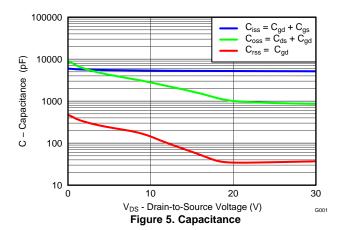


Figure 3. Transfer Characteristics





6 $R_{DS(on)}$ - On-State Resistance $(m\Omega)$ 1

 $I_{D} = 250uA$

T_C - Case Temperature (°C) Figure 6. Threshold Voltage vs. Temperature

75

125

175

25

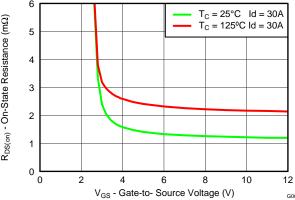


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

-25



TYPICAL MOSFET CHARACTERISTICS (continued)

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

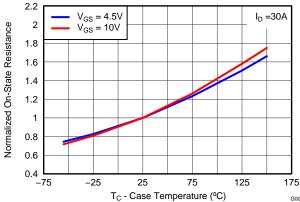


Figure 8. Normalized On-State Resistance vs. Temperature

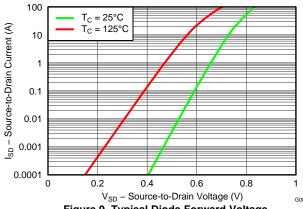


Figure 9. Typical Diode Forward Voltage

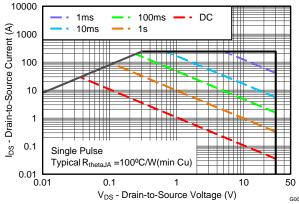


Figure 10. Maximum Safe Operating Area

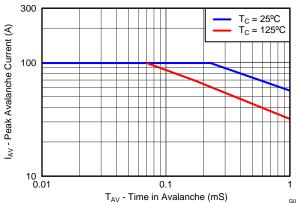


Figure 11. Single Pulse Unclamped Inductive Switching

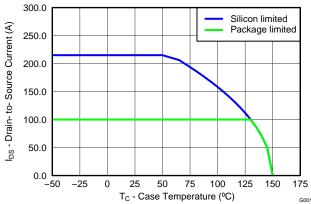


Figure 12. Maximum Drain Current vs. Temperature

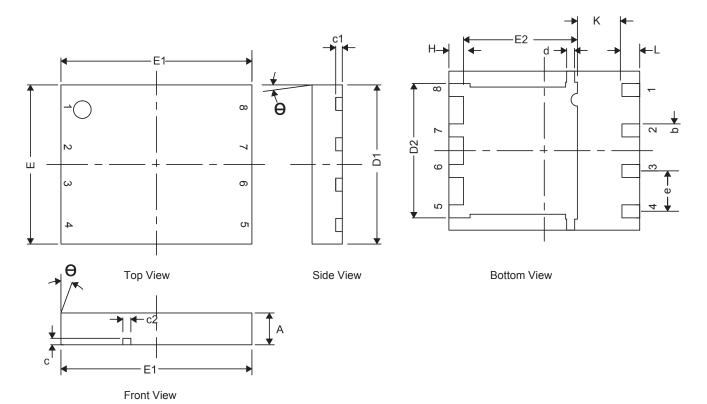
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MECHANICAL DATA

Q5B Package Dimensions



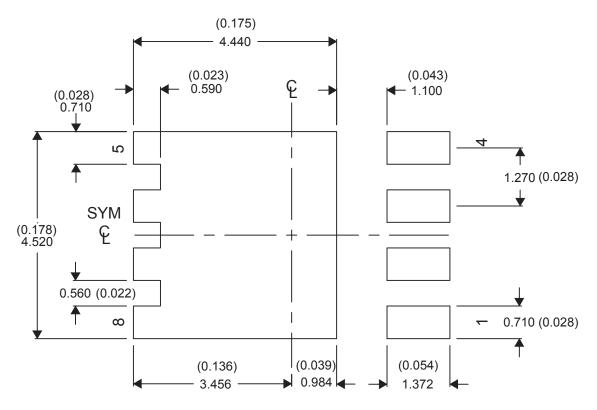
5114	MILLIMETERS								
DIM	MIN	NOM	MAX						
A	0.80	1.00	1.05						
b	0.36	0.41	0.46						
С	0.15	0.20	0.25						
c1	0.15	0.20	0.25						
c2	0.20	0.25	0.30						
D1	4.90	5.00	5.10						
D2	4.12	4.22	4.32						
d	0.20	0.25	0.30						
Е	4.90	5.00	5.10						
E1	5.90	6.00	6.10						
E2	3.48	3.58	3.68						
е		1.27 TYP							
Н	0.360	0.460	0.560						
L	0.46	0.56	0.66						
θ	0°	-	-						
К	1.40 TYP								

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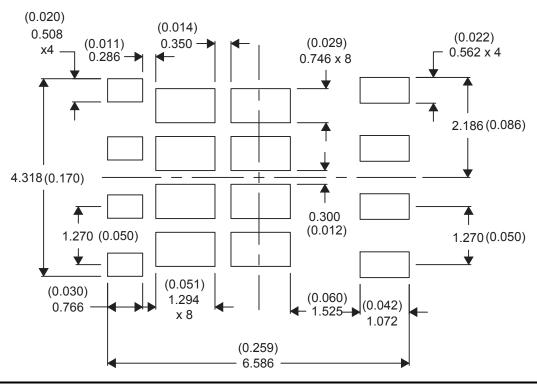


Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Recommended Stencil Pattern

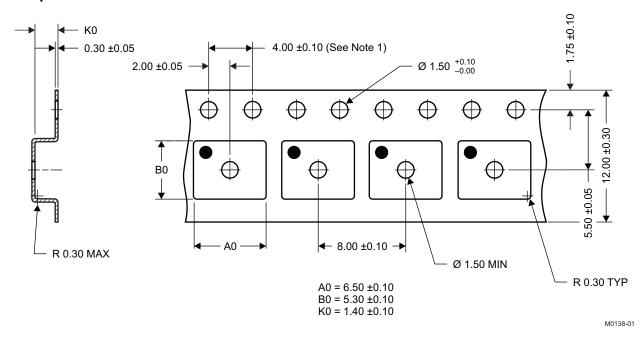


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Q5B Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

REVISION HISTORY

Changes from Original (March 2013) to Revision A

Page

Updated the Dimensions table in the Mechanical Data Section to include DIM "H" values



PACKAGE OPTION ADDENDUM

9-Oct-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
CSD17556Q5B	ACTIVE	VSON	DNK	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD17556	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17556Q5B	VSON	DNK	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CSD17556Q5B	VSON	DNK	8	2500	335.0	335.0	32.0	

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